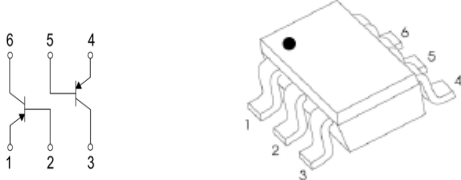


DUAL TRANSISTOR (PNP+PNP)	SOT-363 Plastic-Encapsulate Transistors
<p style="text-align: center;"><u>SOT-363</u></p>  <p style="text-align: center;">Marking :3F</p>	<p>Features</p> <ul style="list-style-type: none"> • Two transistors in one package • Reduces number of components and board space • No mutual interference between the transistors

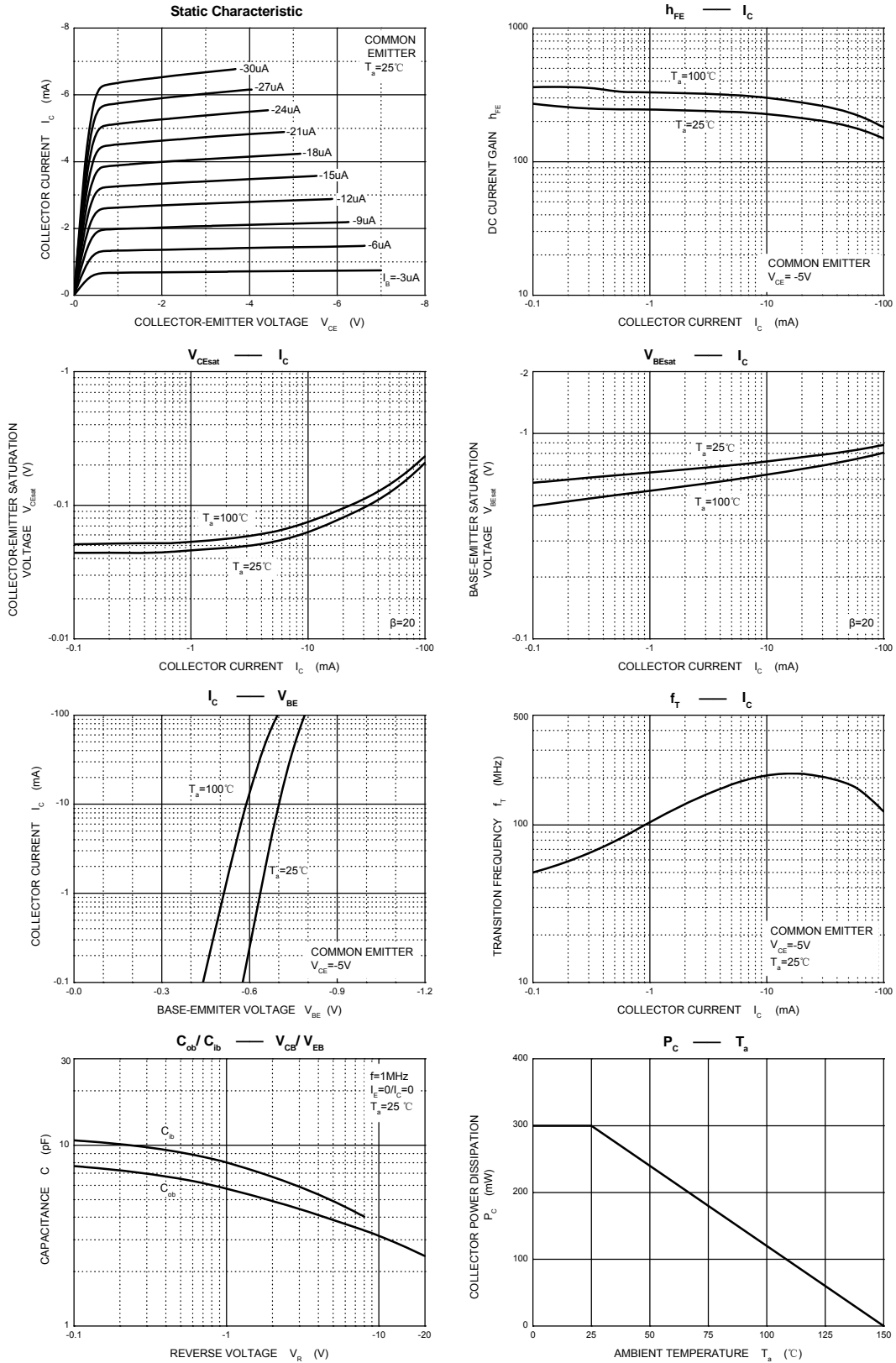
MAXIMUM RATINGS(T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Units
V _{CBO}	Collector- Base Voltage	-50	V
V _{CEO}	Collector-Emitter Voltage	-45	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current -Continuous	-0.2	A
P _C	Collector Power Dissipation	0.3	W
R _{θJA}	Thermal Resistance from Junction to Ambient	417	°C/W
T _J , T _{stg}	Operation Junction and Storage Temperature Range	-55~+150	°C

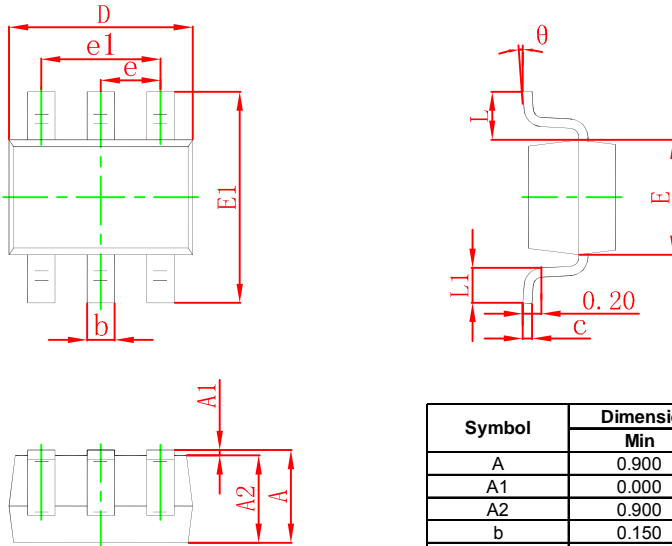
ELECTRICAL CHARACTERISTICS(T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-10μA, I _E =0	-50			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =-10mA, I _B =0	-45			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-10μA, I _C =0	-5			V
Collector cut-off current	I _{CBO}	V _{CB} =-30V, I _E =0			-15	nA
DC current gain	h _{FE}	V _{CE} =-5V, I _C =-2mA	125		630	
Collector-emitter saturation voltage	V _{CE(sat)(1)}	I _C =-10mA, I _B =-0.5mA			-0.3	V
	V _{CE(sat)(2)}	I _C =-100mA, I _B =-5mA			-0.65	V
Base-emitter voltage	V _{BE(1)}	V _{CE} =-5V, I _C =-2mA	-0.6		-0.75	V
	V _{BE(2)}	V _{CE} =-5V, I _C =-10mA			-0.82	V
Transition frequency	f _T	V _{CE} =-5V, I _C =-10mA, f=100MHz		200		MHz
Collector output capacitance	C _{ob}	V _{CB} =-10V, I _E =0, f=1MHz		3.5		pF
Noise figure	NF	V _{CE} =-5V, I _C =-0.2mA, f=1kHz, R _s =2KΩ, BW=200Hz		2.5		dB

Typical Characteristics

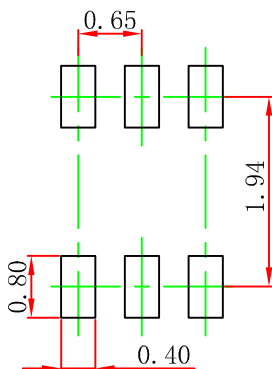


SOT-363 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.150	0.350	0.006	0.014
c	0.080	0.150	0.003	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.450	0.085	0.096
e	0.650 TYP		0.026 TYP	
e1	1.200	1.400	0.047	0.055
L	0.525 REF		0.021 REF	
L1	0.260	0.460	0.010	0.018
theta	0°	8°	0°	8°

SOT-363 Suggested Pad Layout



- Note:
1. Controlling dimension: in millimeters.
 2. General tolerance: ± 0.05 mm.
 3. The pad layout is for reference purposes only.

单击下面可查看定价，库存，交付和生命周期等信息

[>>DIOS\(迪恩思\)](#)